DISCRETE SEMICONDUCTORS

DATA SHEET

BUJ105ASilicon Diffused Power Transistor

Product specification

February 1999



Silicon Diffused Power Transistor

BUJ105A

GENERAL DESCRIPTION

High-voltage, high-speed planar-passivated npn power switching transistor in TO220AB envelope intended for use in high frequency electronic lighting ballast applications, converters, inverters, switching regulators, motor control systems, etc.

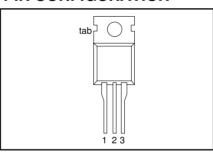
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0 \text{ V}$	-	700	V
V _{CBO}	Collector-Base voltage (open emitter)		-	700	V
V _{CEO}	Collector-emitter voltage (open base)		-	400	V
I _C	Collector current (DC)		-	8	Α
1 1	Collector current peak value		-	16	Α
Piot	Total power dissipation	$T_{mb} \le 25 ^{\circ}C$	-	80	W
P _{tot} V _{CEsat}	Collector-emitter saturation voltage	$I_{\rm C} = 4.0 \text{ A}; I_{\rm B} = 0.8 \text{ A}$	0.3	1.0	V
h _{FEsat}		$I_{\rm C} = 4.0 \text{ A}; V_{\rm CE} = 5 \text{ V}$	11	15	
t, Loui	Fall time	$I_{C} = 5 \text{ A}; I_{B1} = 1 \text{ A}$	20	50	ns

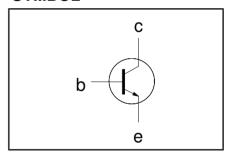
PINNING - TO220AB

PIN	DESCRIPTION	
1	oase	
2	collector	
3	emitter	
tab	collector	

PIN CONFIGURATION



SYMBOL



LIMITING VALUES8

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CESM}	Collector to emitter voltage	$V_{BE} = 0 V$	-	700	V
V _{CEO}	Collector to emitter voltage (open base)		-	400	V
V _{CBO}	Collector to base voltage (open emitter)		-	700	V
l _C	Collector current (DC)		-	8	Α
I I _{CM}	Collector current peak value		-	16	Α
I I _B	Base current (DC)		-	4	Α
I I _{BM}	Base current peak value		-	8	Α
P _{tot}	Total power dissipation	T _{mb} ≤ 25 °C	-	80	W
T _{stg}	Storage temperature		-65	150	°C
T _i	Junction temperature		-	150	°C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
R _{th i-mb}	Junction to mounting base		-	1.56	K/W
R _{th i-a}	Junction to ambient	in free air	60	-	K/W

NXP Semiconductors Product specification

Silicon Diffused Power Transistor

BUJ105A

STATIC CHARACTERISTICS

 T_{mb} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CES} ,I _{CBO}	Collector cut-off current ¹	$\label{eq:VBE} \begin{array}{l} V_{\text{BE}} = 0 \; V; \; V_{\text{CE}} = V_{\text{CESMmax}} \\ V_{\text{BE}} = 0 \; V; \; V_{\text{CE}} = V_{\text{CESMmax}}; \\ T_{j} = 125 \; ^{\circ}\text{C} \end{array}$		-	0.2 0.5	mA mA
I _{CEO} I _{EBO} V _{CEOsust}	Collector cut-off current Emitter cut-off current Collector-emitter sustaining voltage	$ \begin{array}{l} V_{CEO} = V_{CEOMmax} (400V) \\ V_{EB} = 9 V; I_{C} = 0 A \\ I_{B} = 0 A; I_{C} = 10 mA; \\ L = 25 mH \end{array} $	- - 400	- - -	0.1 1 -	mA mA V
V _{CEsat} V _{BEsat} h _{FE} h _{FE} h _{FEsat}	Collector-emitter saturation voltage Base-emitter saturation voltage DC current gain	$\begin{aligned} &I_{C} = 4.0 \text{ A;} I_{B} = 0.8 \text{ A} \\ &I_{C} = 4.0 \text{ A;} I_{B} = 0.8 \text{ A} \\ &I_{C} = 1 \text{ mA;} \text{ V}_{CE} = 5 \text{ V} \\ &I_{C} = 500 \text{ mA;} \text{ V}_{CE} = 5 \text{ V} \\ &I_{C} = 4.0 \text{ A;} \text{ V}_{CE} = 5 \text{ V} \end{aligned}$	- - 10 13 8	0.3 1.0 14 23 11	1.0 1.5 34 36 15	V V

DYNAMIC CHARACTERISTICS

 T_{mb} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
	Switching times (resistive load)	$I_{Con} = 5 \text{ A}; I_{Bon} = -I_{Boff} = 1 \text{ A}; R_L = 75 \text{ ohms}; V_{BB2} = 4 \text{ V};$			
t _{on} t _s t _f	Turn-on time Turn-off storage time Turn-off fall time	L , 55L ,	0.65 1.8 0.3	1 2.5 0.5	μs μs μs
	Switching times (inductive load)	$I_{Con} = 5 \text{ A}; I_{Bon} = 1 \text{ A}; L_{B} = 1 \mu\text{H}; $			
t _s t _f	Turn-off storage time Turn-off fall time	ABB — O A	1.2 20	1.7 50	μs ns
	Switching times (inductive load)	$I_{Con} = 5 \text{ A}; I_{Bon} = 1 \text{ A}; L_{B} = 1 \mu\text{H}; \\ -V_{BB} = 5 \text{ V}; T_{i} = 100 ^{\circ}\text{C}$			
t _s t _f	Turn-off storage time Turn-off fall time	, , , , , , , , , , , , , , , , , , ,	1.4 25	1.9 100	μs ns

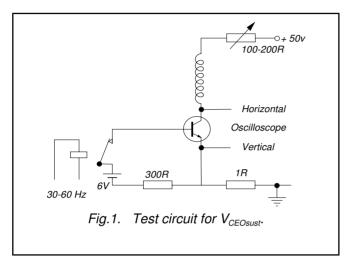
February 1999 2 Rev 1.000

¹ Measured with half sine-wave voltage (curve tracer).

NXP Semiconductors Product specification

Silicon Diffused Power Transistor

BUJ105A



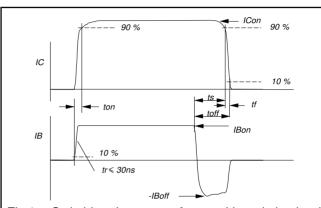
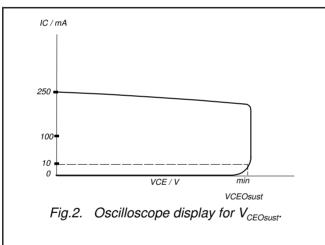
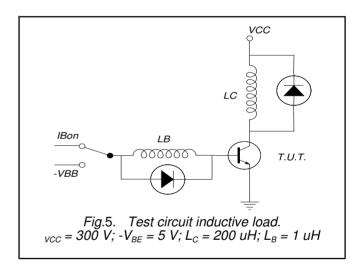
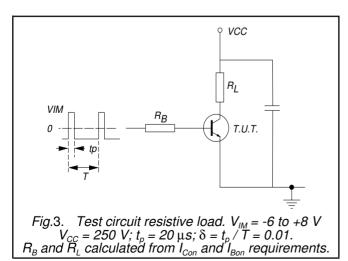
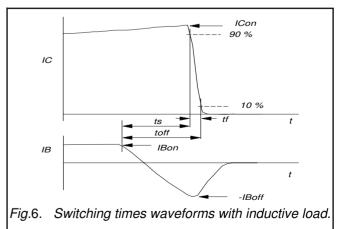


Fig.4. Switching times waveforms with resistive load.



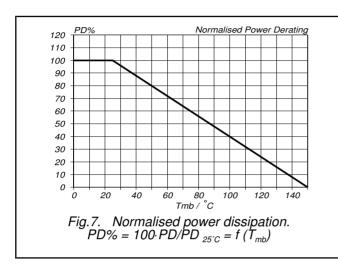


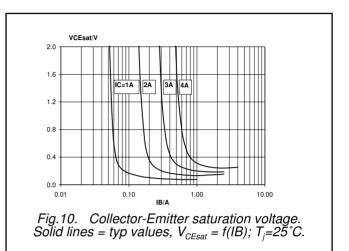


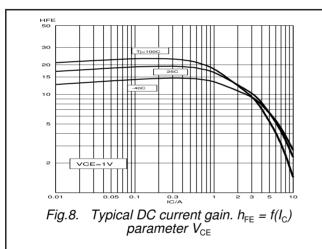


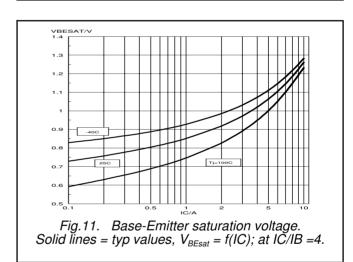
Silicon Diffused Power Transistor

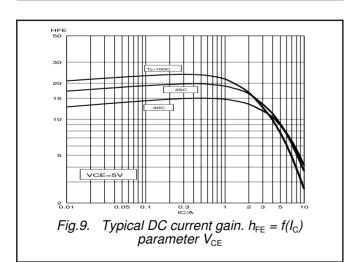
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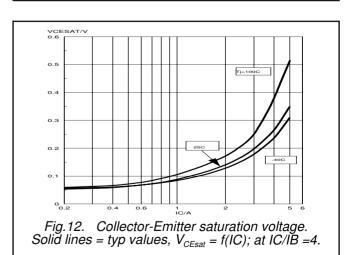










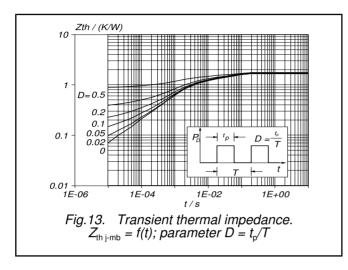


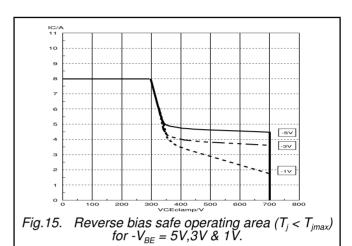
February 1999 4 Rev 1.000

NXP Semiconductors Product specification

Silicon Diffused Power Transistor

BUJ105A





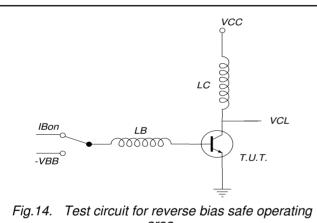


Fig.14. Test circuit for reverse bias safe operating area.

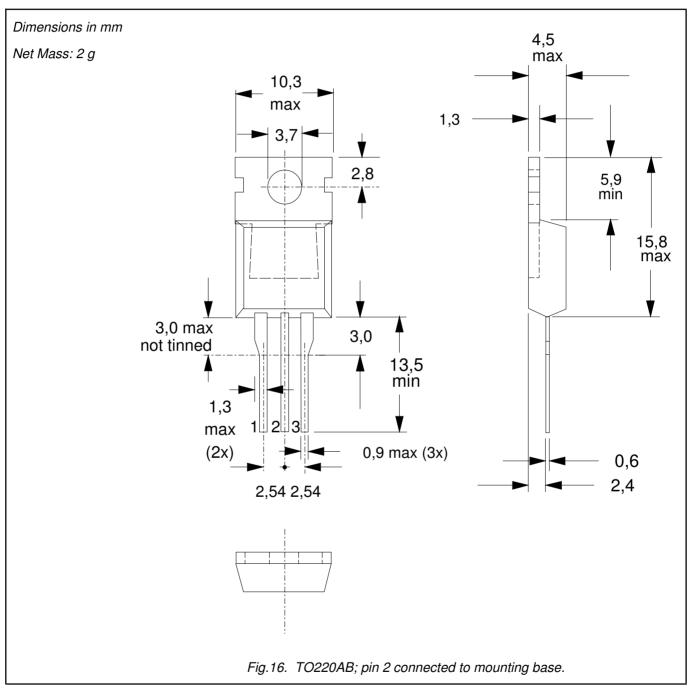
$$\begin{split} V_{clamp} < 700V; \ V_{cc} = 150V; \ -V_{be} = 5V, 3V \ \& \ 1V; \\ L_B = 1 \mu H; \ L_C = 200 \mu H. \end{split}$$

NXP Semiconductors Product specification

Silicon Diffused Power Transistor

BUJ105A

MECHANICAL DATA



- Notes
 1. Refer to mounting instructions for TO220 envelopes.
 2. Epoxy meets UL94 V0 at 1/8".

Legal information

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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